CLAIM(S):

1. A chemical mechanical polishing composition comprising:

an aqueous based liquid carrier;

abrasive particles dispersed in the liquid carrier, wherein the abrasive particles comprise colloidal silica abrasive particles;

0.05 weight percent to 0.5 weight percent of a dipolar aprotic solvent, wherein the dipolar aprotic solvent is dimethyl sulfoxide; and

a pH in a range from about 8 to about 12.

2. The composition of claim 1, further comprising one or more organic carboxylic acids.

3. The composition of claim 1, further comprising one or more polyaminocarboxylic acids.

4. The composition of claim 1, further comprising one or more tetraalkylammonium salts.

5. The composition of claim 1, further comprising one or more aminophosphonic acids.

6. The composition of claim 1, further comprising one or more nitrogen containing heterocyclic compounds.

7. The composition of claim 1, further comprising:

one or more tetraalkylammonium salts;

one or more polyaminocarboxylic acids; and

one or more nitrogen containing heterocyclic compounds.

8. The composition of claim 7, further comprising at least one of potassium hydroxide and potassium bicarbonate.

9. A method of chemical mechanical polishing a wafer, the method comprising:

(a) contacting the wafer with the polishing composition of any one of claims 1-8;

(b) moving the polishing composition relative to the wafer; and

(c) abrading the wafer to remove silicon from the wafer and thereby polish the wafer.

10. The method of claim 9, wherein

the method uses a polishing apparatus having (i) an upper platen and a lower platen, each of said platens having a polishing pad adhered thereto, and (ii) a carrier plate having at least one holding hole for holding the wafer; and

said abrading in (c) removes silicon from opposing first and second sides of the wafer, thereby polishing the wafer.

11. The method of claim 9, wherein:

the wafer includes a hard laser mark; and

said abrading in (c) improves a flatness of the wafer in a peripheral region of the wafer.

12. A chemical-mechanical polishing concentrate comprising:

a water based liquid carrier;

abrasive particles dispersed in the liquid carrier, wherein the abrasive particles comprise colloidal silica particles;

0.05 weight percent to 0.5 weight percent of a dipolar aprotic solvent, wherein the dipolar aprotic solvent is dimethyl sulfoxide; and a pH in a range from about 8 to about 12.

13. The polishing concentrate of claim 12, wherein:

the polishing concentrate comprises at least 10 weight percent of the colloidal silica particles.

14. A method of chemical mechanical polishing a wafer, the method comprising:

(a) providing a polishing concentrate including: (i) a water based liquid carrier, (ii) at least 5 weight percent colloidal silica particles dispersed in the liquid carrier; and (iii) a pH in a range from about 8 to about 12;

(b) diluting the polishing concentrate provided in (a) to obtain a polishing composition by adding at least 4 parts of a mixture of water and a dipolar aprotic solvent to 1 part of the polishing concentrate such that the polishing composition includes 0.05 weight percent to 0.5 weight percent of the dipolar aprotic solvent, wherein the dipolar aprotic solvent is dimethyl sulfoxide;

(c) moving the polishing composition relative to the wafer; and

(d) abrading the wafer to remove silicon from the wafer and thereby polish the wafer.

15. The method of claim 14, wherein

the method uses a polishing apparatus having (i) an upper platen and a lower platen, each of said platens having a polishing pad adhered thereto, and (ii) a carrier plate having at least one holding hole for holding the wafer; and

said abrading in (d) removes silicon from opposing first and second sides of the wafer, thereby polishing the wafer.